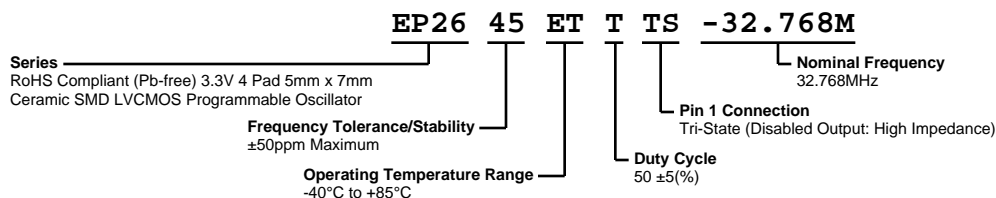


EP2645ETTS-32.768M



ECLIPTEK
CORPORATION



ELECTRICAL SPECIFICATIONS

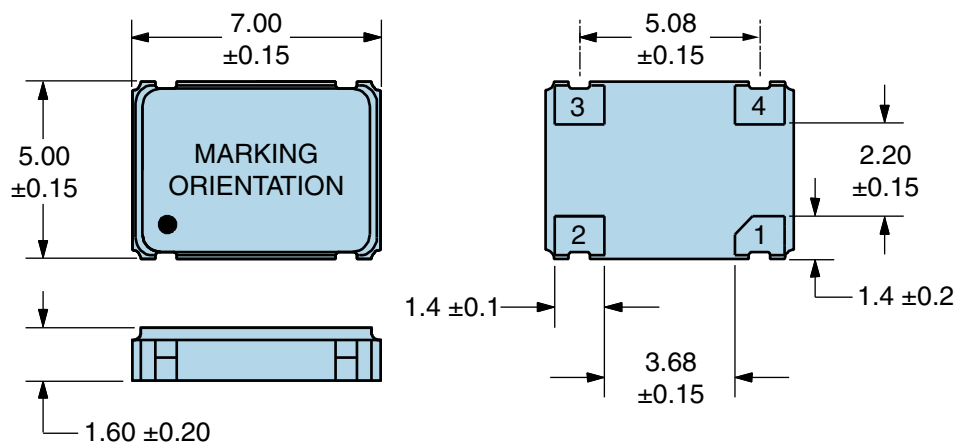
Nominal Frequency	32.768MHz
Frequency Tolerance/Stability	± 50 ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	± 5 ppm/year Maximum
Operating Temperature Range	-40°C to +85°C
Supply Voltage	3.3Vdc ± 0.3 Vdc
Input Current	28mA Maximum (Unloaded)
Output Voltage Logic High (Voh)	Vdd-0.4Vdc Minimum (IOH= -8mA)
Output Voltage Logic Low (Vol)	0.4Vdc Maximum (IOL= +8mA)
Rise/Fall Time	4nSec Maximum (Measured at 20% to 80% of waveform)
Duty Cycle	50 \pm 5(%) (Measured at 50% of waveform)
Load Drive Capability	30pF Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (Disabled Output: High Impedance)
Tri-State Input Voltage (Vih and Vil)	70% of Vdd Minimum to enable output, 20% of Vdd Maximum to disable output, No Connect to enable output.
Standby Current	20 μ A Maximum (Pin 1 = Ground)
Disable Current	16mA Maximum (Pin 1 = Ground)
Absolute Clock Jitter	± 250 pSec Maximum, ± 100 pSec Typical
One Sigma Clock Period Jitter	± 50 pSec Maximum
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V
Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Flammability	UL94-V0
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-883, Method 2002, Condition B
Moisture Resistance	MIL-STD-883, Method 1004
Moisture Sensitivity	J-STD-020, MSL 1
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010, Condition B
Vibration	MIL-STD-883, Method 2007, Condition A

EP2645ETTS-32.768M

MECHANICAL DIMENSIONS (all dimensions in millimeters)

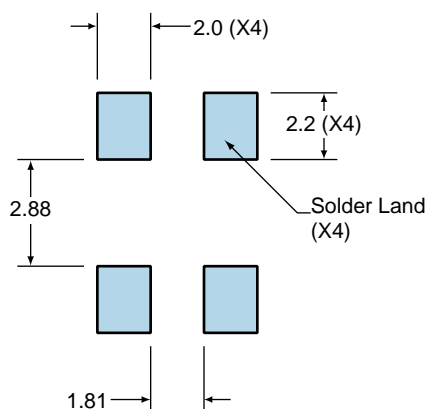


PIN	CONNECTION
1	Tri-State (High Impedance)
2	Ground/Case Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	32.768M
3	PXXYYZ P=Configuration Designator XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year

Suggested Solder Pad Layout

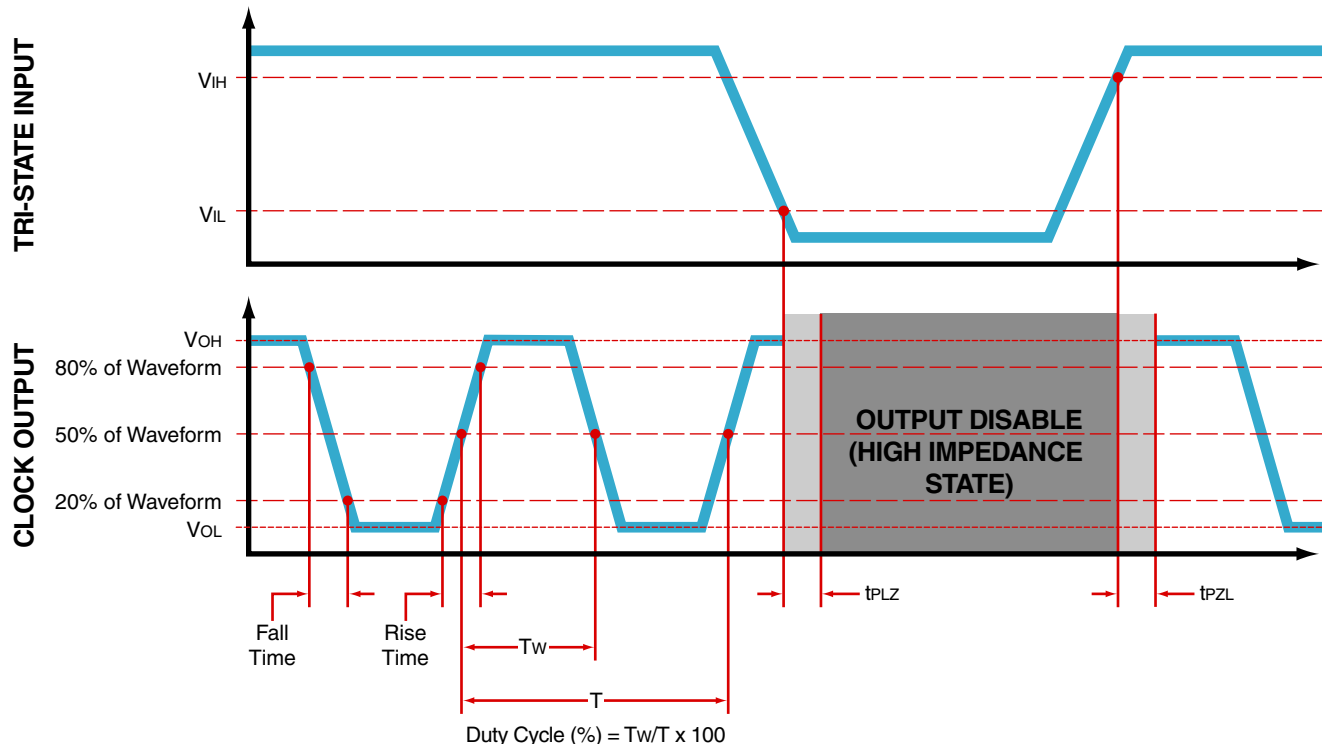
All Dimensions in Millimeters



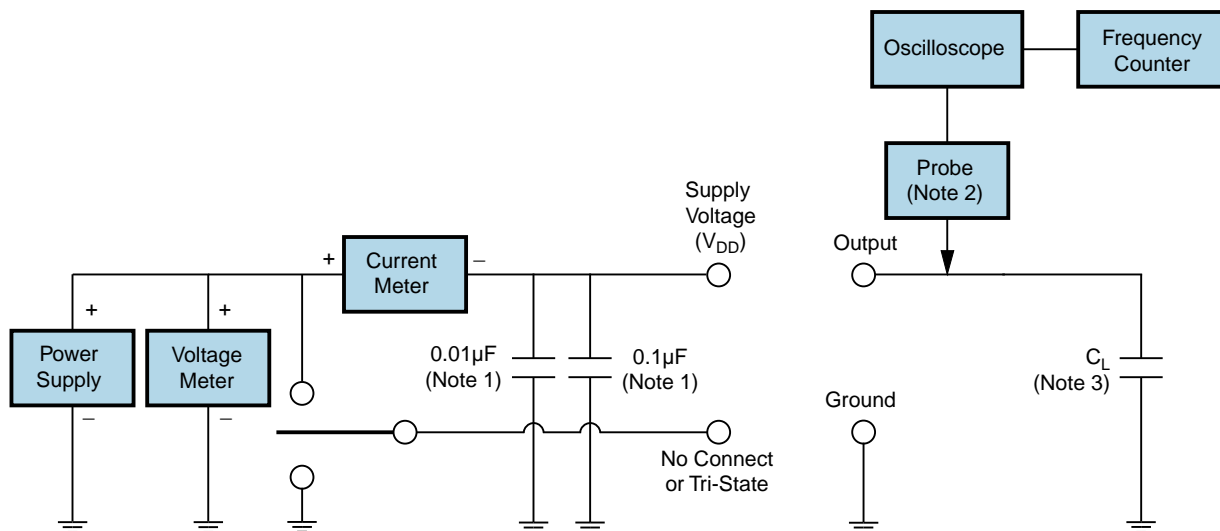
All Tolerances are ± 0.1

EP2645ETTS-32.768M

OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



Note 1: An external $0.1\mu\text{F}$ low frequency tantalum bypass capacitor in parallel with a $0.01\mu\text{F}$ high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance ($<12\text{pF}$), 10X attenuation factor, high impedance ($>10\text{Mohms}$), and high bandwidth ($>300\text{MHz}$) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

Recommended Solder Reflow Methods



High Temperature Infrared/Convection

$T_s \text{ MAX to } T_L$ (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum ($T_s \text{ MIN}$)	150°C
- Temperature Typical ($T_s \text{ TYP}$)	175°C
- Temperature Maximum ($T_s \text{ MAX}$)	200°C
- Time ($t_s \text{ MIN}$)	60 - 180 Seconds
Ramp-up Rate (T_L to T_p)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T_L)	217°C
- Time (t_L)	60 - 150 Seconds
Peak Temperature (T_p)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature ($T_p \text{ Target}$)	250°C +0/-5°C
Time within 5°C of actual peak (t_p)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

T_S MAX to T_L (Ramp-up Rate)	5°C/second Maximum
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Preheat

- Temperature Minimum (T_S MIN)	N/A
- Temperature Typical (T_S TYP)	150°C
- Temperature Maximum (T_S MAX)	N/A
- Time (t_s MIN)	60 - 120 Seconds

Ramp-up Rate (T_L to T_P)	5°C/second Maximum
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Time Maintained Above:

- Temperature (T_L)	150°C
- Time (t_L)	200 Seconds Maximum

Peak Temperature (T_P)	240°C Maximum
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Target Peak Temperature (T_P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
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Time within 5°C of actual peak (t_p)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
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Ramp-down Rate	5°C/second Maximum
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Time 25°C to Peak Temperature (t)	N/A
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Moisture Sensitivity Level	Level 1
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Additional Notes	Temperatures shown are applied to body of device.
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Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)